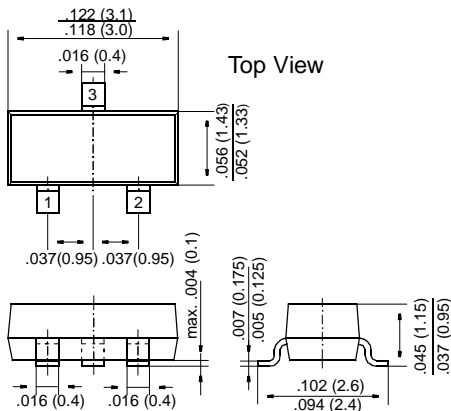


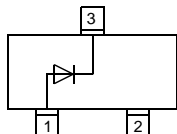
BAS70 THRU BAS70-06

Schottky Diodes

SOT-23



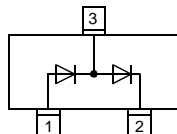
Dimensions in inches and (millimeters)



Top View

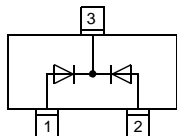
BAS70

Marking: 73



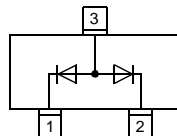
BAS70-04

Marking: 74



BAS70-05

Marking: 75



BAS70-06

Marking: 76

FEATURES

- ◆ These diodes feature very low turn-on voltage and fast switching.
- ◆ These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges.



MECHANICAL DATA

Case: SOT-23 Plastic Package

Weight: approx. 0.008 g

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS FOR ONE DIODE

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	70	V
Forward Continuous Current at $T_{amb} = 25\text{ °C}$	I_F	200 ¹⁾	mA
Surge Forward Current at $t_p < 1\text{ s}$, $T_{amb} = 25\text{ °C}$	I_{FSM}	600 ¹⁾	mA
Power Dissipation ¹⁾ at $T_{amb} = 25\text{ °C}$	P_{tot}	200 ¹⁾	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_S	-55 to +150	°C

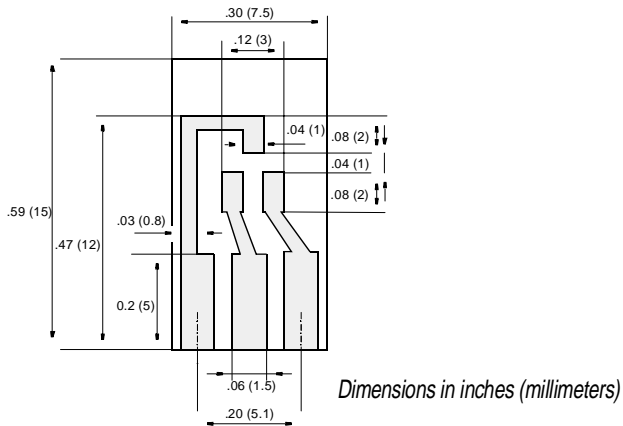
¹⁾ Device on fiberglass substrate, see layout

BAS70 THRU BAS70-06

ELECTRICAL CHARACTERISTICS

Ratings for one diode at 25 °C ambient temperature unless otherwise specified

	Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage Tested with 10 μ A Pulses	$V_{(BR)R}$	70	–	–	V
Leakage Current Pulse Test $t_p < 300 \mu s$ at $V_R = 50 V$	I_R	–	20	100	nA
Forward Voltage Pulse Test $t_p < 300 \mu s$ at $I_F = 1 mA$ at $I_F = 15 mA$	V_F V_F	– –	– –	410 1000	mV mV
Capacitance at $V_R = 0 V, f = 1 MHz$	C_{tot}	–	1.5	2	pF
Reverse Recovery Time from $I_F = 10 mA$ through $I_R = 10 mA$ to $I_R = 1 mA$	t_{rr}	–	–	5	ns
Thermal Resistance Junction to Ambient Air	R_{thJA}	–	–	430 ¹⁾	K/W
1) Device on fiberglass substrate, see layout					



Layout for R_{thJA} test

Thickness: Fiberglass 0.059 in (1.5 mm)

Copper leads 0.012 in (0.3 mm)